



### Description

The DGD2012 is a mid-voltage / high-speed gate driver capable of driving N-Channel MOSFETs in a half-bridge configuration. Highvoltage processing techniques enable the DGD2012's high-side to switch to 200V in a bootstrap operation.

The DGD2012 logic inputs are compatible with standard TTL and CMOS levels (down to 3.3V) to interface easily with controlling devices. The driver outputs feature high pulse current buffers designed for minimum driver cross conduction.

The DGD2012 is available in a space saving SO-8 package and operates over an extended -40°C to +125°C temperature range.

### Applications

- Battery Power Tools and Appliances
- Light Electric Vehicles (LEV)
- Inverters

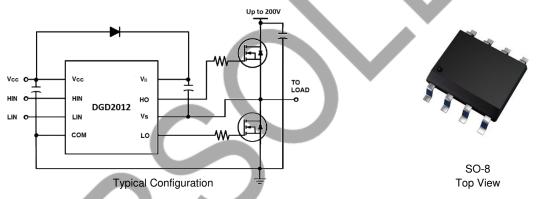
**HIGH-SIDE AND LOW-SIDE GATE DRIVER IN SO-8** 

#### Features

- Floating High-Side Driver in Bootstrap Operation to 200V
- Drives Two N-Channel MOSFETs in Half Bridge Configuration
- 1.9A Source / 2.3A Sink Output Current Capability
- **Outputs Tolerant to Negative Transients**
- Wide Low-Side Gate Driver Supply Voltage: 10V to 20V
- Logic Input (HIN and LIN) 3.3V Capability
- Schmitt Triggered Logic Inputs with Internal Pull Down •
- Undervoltage Lockout for High-Side and Low-Side Drivers
- Extended Temperature Range: -40°C to +125°C
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/guality/product-definitions/

### **Mechanical Data**

- Case: SO-8 (Type TH)
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 3 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads. Solderable per MIL-STD-202, Method 208 3
- Weight: 0.075 grams (Approximate)



### Ordering Information (Note 4)

Part Number	Marking Code	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
DGD2012S8-13	DGD2012	13	12	2500

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + CI) and <1000ppm antimony compounds. 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

### Marking Information

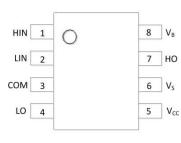
Notes:



Characteria Control Contro DGD2012 = Product Type Marking Code YY = Year (ex: 21 = 2021) WW = Week (01 to 53)



### **Pin Diagrams**

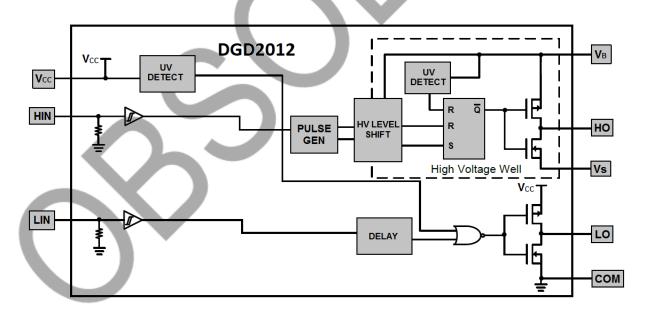




## **Pin Descriptions**

Pin Number	Pin Name	Function
1	HIN	Logic Input for High-Side Gate Driver Output, in Phase with HO
2	LIN	Logic Input for Low-Side Gate Driver Output, in Phase with LO
3	COM	Low-Side and Logic Return
4	LO	Low-Side Gate Drive Output
5	Vcc	Low-Side and Logic Fixed Supply
6	Vs	High-Side Floating Supply Return
7	HO	High-Side Gate Drive Output
8	VB	High-Side Floating Supply

## **Functional Block Diagram**





# Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
High-Side Floating Supply Voltage	VB	-0.3 to +224	V	
High-Side Floating Supply Offset Voltage	Vs	V <sub>B</sub> -24 to V <sub>B</sub> +0.3	V	
High-Side Floating Output Voltage	Vно	Vs-0.3 to V <sub>B</sub> +0.3	V	
Offset Supply Voltage Transient	dVs / dt	50	V/ns	
Low-Side and Logic Fixed Supply Voltage	V <sub>CC</sub>	-0.3 to +24	V	
Low-Side Output Voltage	VLO	-0.3 to Vcc+0.3	V	
Logic Input Voltage (HIN and LIN)	V <sub>IN</sub>	-0.3 to V <sub>CC</sub> +0.3	V	

### Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Currente al	Value	Unit
Characteristic	Symbol	Value	Unit
Power Dissipation Linear Derating Factor (Note 5)	PD	0.625	W
Thermal Resistance, Junction to Ambient (Note 5)	Reja	200	°C/W
Operating Temperature	TJ	+150	
Lead Temperature (Soldering, 10s)	TL 🖌	+300	°C
Storage Temperature Range	Тѕтд	-55 to +150	

Note: 5. When mounted on a standard JEDEC 2-layer FR-4 board.

### **Recommended Operating Conditions**

Parameter	Symbol	Min	Max	Unit
High Side Floating Supply Absolute Voltage	VB	Vs + 10	V <sub>S</sub> + 20	V
High Side Floating Supply Offset Voltage	Vs	(Note 6)	200	V
High Side Floating Output Voltage	VHO	Vs	VB	V
Low Side and Logic Fixed Supply Voltage	Vcc	10	20	V
Low Side Output Voltage	VLO	0	Vcc	V
Logic Input Voltage	VIN	0	5	V
Ambient Temperature	TA	-40	+125	°C

Note: 6. Logic operation for  $V_S$  of -5V to +200V.



# DC Electrical Characteristics (V<sub>BIAS</sub> (V<sub>CC</sub>, V<sub>BS</sub>) = 15V, @T<sub>A</sub> = +25°C, unless otherwise specified.) (Note 7)

Parameter	Symbol	Min	Тур	Max	Unit	Conditions
Logic "1" Input Voltage (Note 8)	VIH	2.5	_	—	V	$V_{CC} = 10V$ to 20V
Logic "0" Input Voltage (Note 8)	VIL	_	_	0.8	V	Vcc = 10V to 20V
High Level Output Voltage, V <sub>BIAS</sub> - V <sub>O</sub>	V <sub>OH</sub>	—	_	1.4	V	$I_{\rm O} = 0$ A
Low Level Output Voltage, Vo	Vol	_	_	0.2	V	I <sub>O</sub> = 20mA
Offset Supply Leakage Current	Ilk	_	_	50	μA	$V_B = V_S = 200V$
Quiescent V <sub>BS</sub> Supply Current	I <sub>BSQ</sub>	20	60	150	μΑ	$V_{IN} = 0V \text{ or } 5V$
Quiescent Vcc Supply Current	lccq	50	120	240	μA	VIN = 0V or 5V
Logic "1" Input Bias Current	lin+	—	25	60	μA	Vin = 5V
Logic "0" Input Bias Current	I <sub>IN-</sub>	_	_	5.0	μA	$V_{IN} = 0V$
VBS Supply Undervoltage Positive Going Threshold	VBSUV+	8.0	8.9	9.8	V	
V <sub>BS</sub> Supply Undervoltage Negative Going Threshold	V <sub>BSUV-</sub>	7.4	8.2	9.0	V	-
Vcc Supply Undervoltage Positive Going Threshold	VCCUV+	8.0	8.9	9.8	V	-
V <sub>CC</sub> Supply Undervoltage Negative Going Threshold	Vccuv-	7.4	8.2	9.0	V	
Output High Short Circuit Pulsed Current	Io+	1.4	1.9	-	A	$V_0 = 0V, PW \le 10\mu s$
Output Low Short Circuit Pulsed Current	I <sub>O-</sub>	1.7	2.3		А	$V_0 = 15V, PW \le 10\mu s$

Notes: 7. The V<sub>IN</sub> and I<sub>IN</sub> parameters are applicable to the two logic pins: HIN and LIN. The V<sub>O</sub> and I<sub>O</sub> parameters are applicable to the respective output pins: HO and LO.

8. For optimal operation, it is recommended that the input pulses (HIN and LIN) should have a minimum amplitude of 2.5V with a minimum pulse width of 360ns.

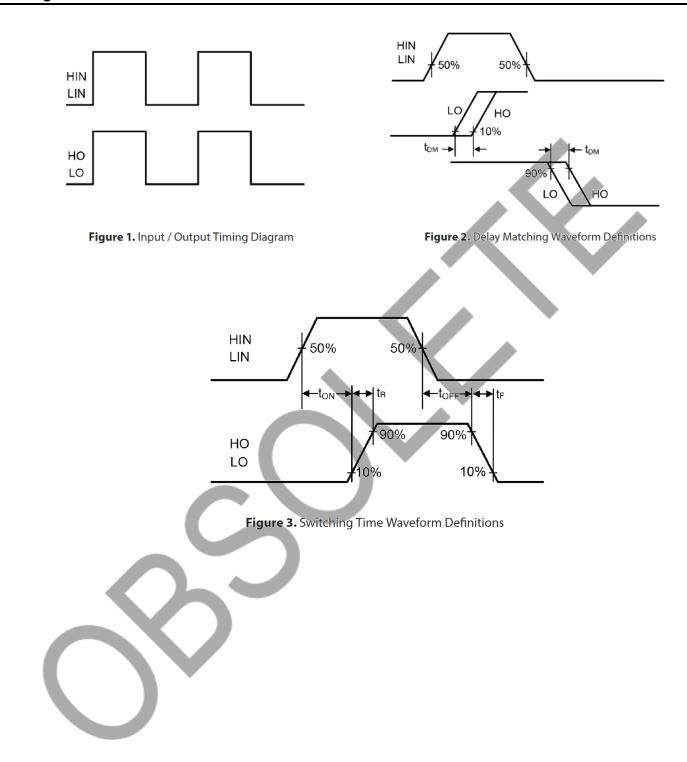
### AC Electrical Characteristics (VBIAS (VCC, VBS) = 15V, CL = 1000pF, @TA = +25°C, unless otherwise specified.)

Parameter	Symbol	Min	Тур	Max	Unit	Conditions
Turn-On Propagation Delay	ton		180	270	ns	$V_S = 0V$
Turn-Off Propagation Delay	toff	-	220	330	ns	Vs = 0V or 200V
Delay Matching, HO & LO Turn-On/Off	tdм			35	ns	—
Turn-On Rise Time	tR	—	40	60	ns	$V_S = 0V$
Turn-Off Fall Time	tF	-	20	35	ns	Vs = 0V





### **Timing Waveforms**





### Typical Performance Characteristics (V<sub>CC</sub> = 15V, @T<sub>A</sub> = +25°C, unless otherwise specified.)

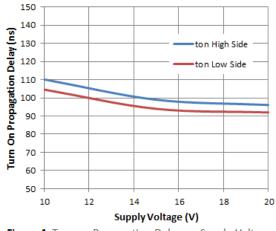


Figure 4. Turn-on Propagation Delay vs. Supply Voltage

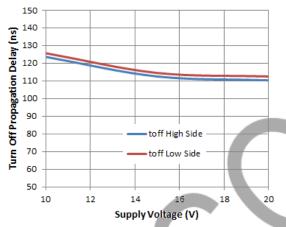
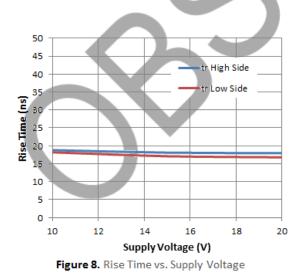


Figure 6. Turn-off Propagation Delay vs. Supply Voltage



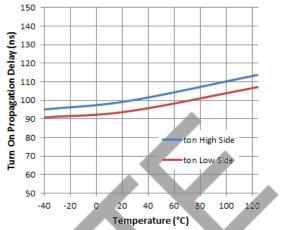


Figure 5. Turn-on Propagation Delay vs. Temperature

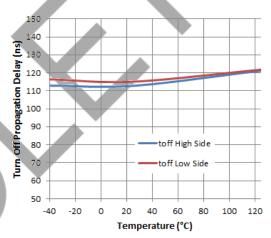
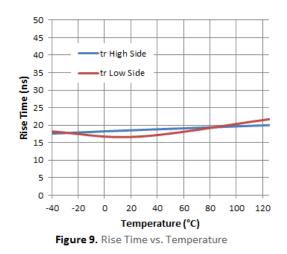
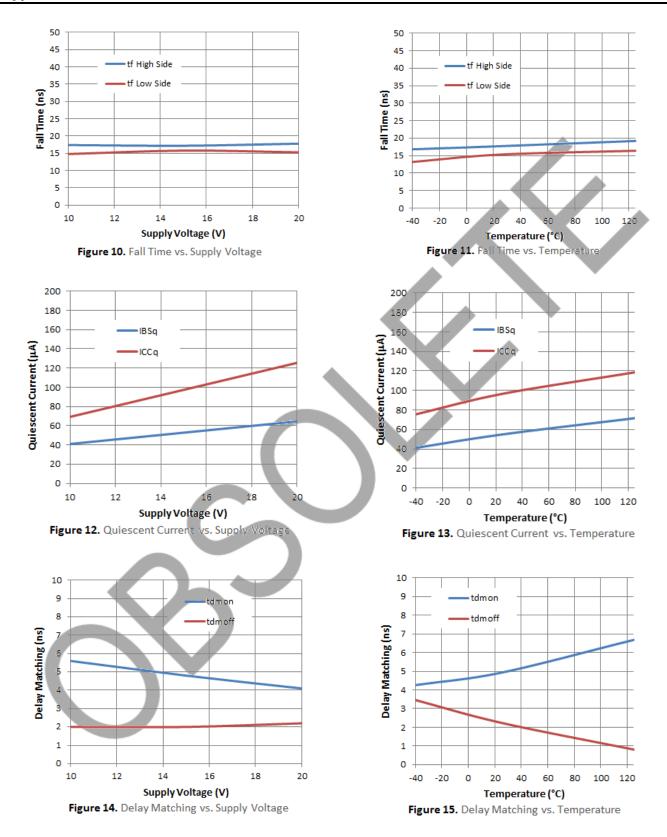


Figure 7. Turn-off Propagation Delay vs. Temperature



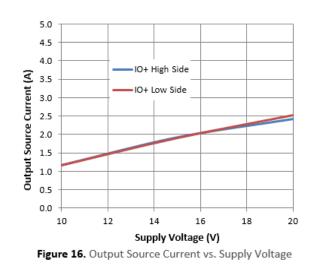


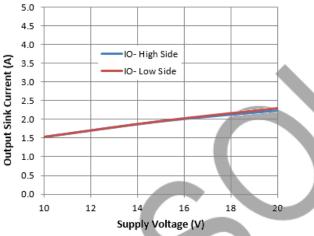
# Typical Performance Characteristics (continued)

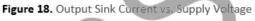




### Typical Performance Characteristics (continued)











2.0 1.5 1.0 0.5 0.0 -20 20 40 60 80 100 120 -40 Temperature (°C)

IO+ High Side

IO+ Low Side

5.0

4.5

4.0

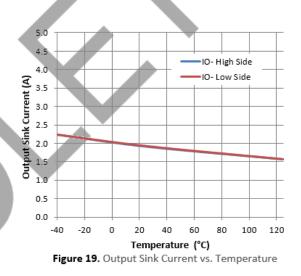
3.5

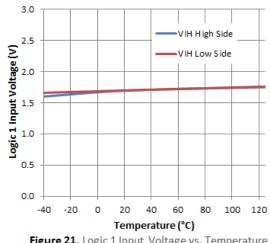
3.0

2.5

Output Source Current (A)

Figure 17. Output Source Current vs. Temperature









VIL High Side

VIL Low Side

80

60

VBSUV+

VBSUV-

60 80 100 120

100 120

0

0

20

40

Temperature (°C)

20

40

Temperature (°C)

### Typical Performance Characteristics (continued)

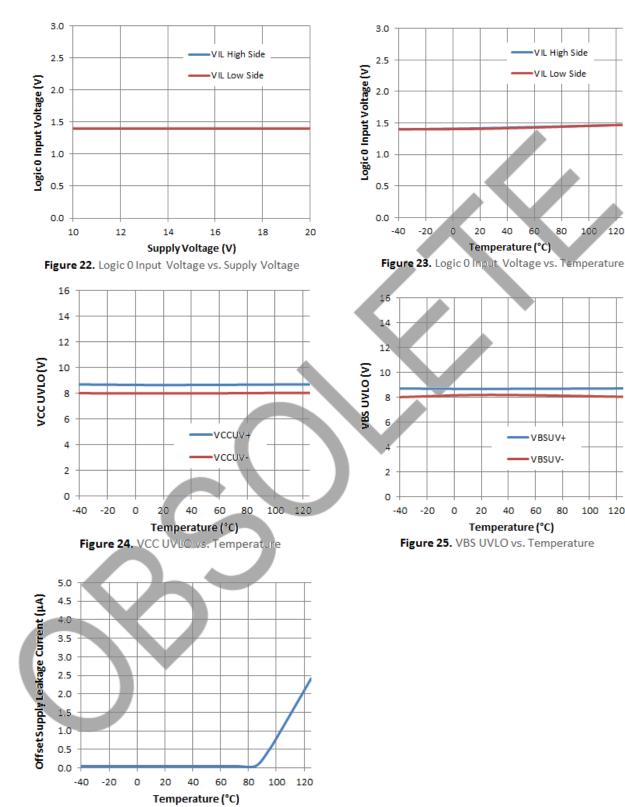
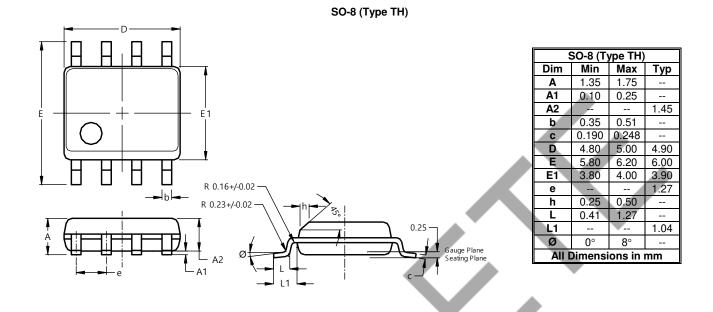


Figure 26. Offset Supply Leakage Current vs. Temperature



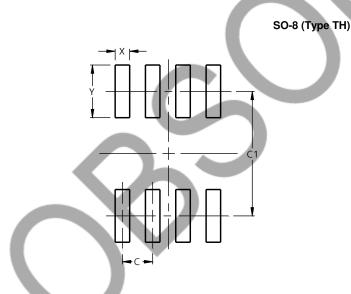
### Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.



### **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)
С	1.27
C1	5.20
Х	0.60
Y	2.20

Note:

: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device Terminals and PCB tracking.



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